

Isc N-Channel MOSFET Transistor

STB22NM60N

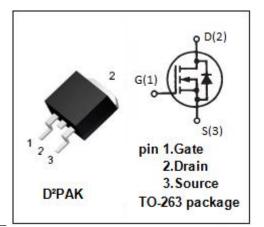
FEATURES

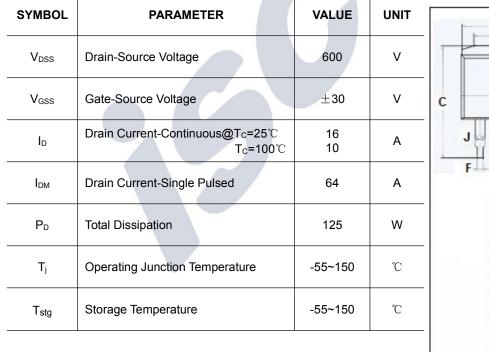
- · Low input capacitance and gate charge
- · Low gate input resistances
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

Switching applications

• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

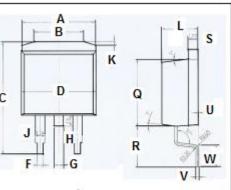


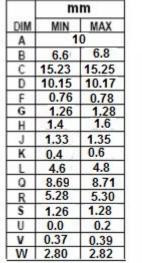


THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT	
Rth(ch-c)	n(ch-c) Channel-to-case thermal resistance		°C/W	

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ELECTRICAL CHARACTERISTICS

$T_{C}\text{=}25^{\circ}\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 1mA	600			V
V _{GS} (th)	Gate Threshold Voltage	V _{DS} =±30V; I _D =0.25mA	2		4	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =8A		200	220	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±25V;V _{DS} = 0V			±0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 600V; V _{GS} = 0V; T _J =25°C T _J =125°C			1 100	μA
V _{SDF}	Diode forward voltage	I _{SD} =16A, V _{GS} = 0 V			1.6	V

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